

BUK9M11-40E

N-channel 40 V, 11 m Ω logic level MOSFET in LFPAK33

19 September 2016

Product data sheet

1. General description

Logic level N-channel MOSFET in an LFPAK33 (Power33) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V_{GS(th)} rating of greater than 0.5 V at 175 °C

3. Applications

- 12 V automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	40	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>	-	-	53	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	-	62	W
Static chara	acteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$	-	9.3	11	mΩ
Dynamic ch	naracteristics					
Q_{GD}	gate-drain charge	I _D = 15 A; V _{DS} = 32 V; V _{GS} = 5 V; T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	5	-	nC



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline		(Graphic symbol
1	S	Source				D I
2	S	Source				
3	S	Source				G T T
4	G	Gate				mbb076 S
mb	D	Mounting base; connected to drain	LI	FPAK33 (SOT1210)		

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BUK9M11-40E	LFPAK33	Plastic single ended surface mounted package (LFPAK33); 8 leads	SOT1210			

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9M11-40E	91140E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	40	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 k Ω		-	40	V
V _{GS}	gate-source voltage	DC; T _j ≤ 175 °C		-10	10	V
		Pulsed; T _j ≤ 175 °C	[1][2]	-15	15	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	62	W
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	53	Α
		V _{GS} = 5 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	37	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; Fig. 3		-	211	Α

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Symbol	Parameter	Conditions		Min	Max	Unit
T _{stg}	storage temperature			-55	175	°C
T _j	junction temperature			-55	175	°C
Source-dra	in diode					
I _S	source current	T _{mb} = 25 °C		-	51	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	211	Α
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 53 A; $V_{sup} \le 40$ V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[3][4]	-	32.4	mJ

- [1] Accumulated pulse duration up to 50 hours delivers zero defect ppm.
- [2] Significantly longer life times are achieved by lowering T_j and or V_{GS}
- [3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [4] Refer to application note AN10273 for further information.

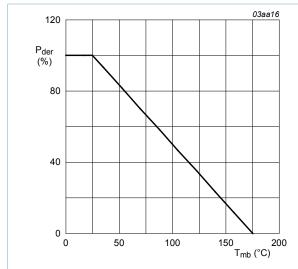


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

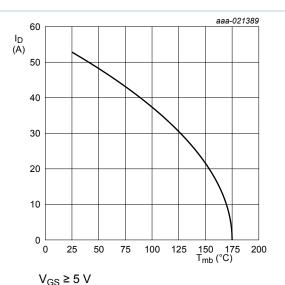
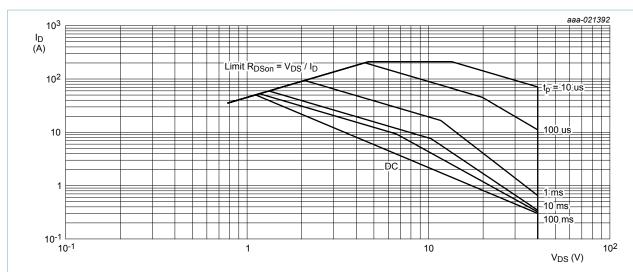


Fig. 2. Continuous drain current as a function of mounting base temperature

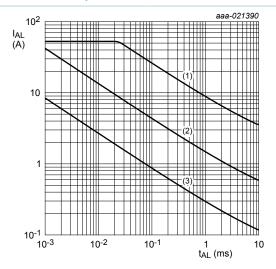
$$I_D = 53A \times \sqrt{\frac{175^{\circ}C - T_{mb}}{150^{\circ}C}}$$
 for $T_{mb} \ge 25^{\circ}C$

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 T_{mb} = 25 °C; I_{DM} is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



(1) $T_{j \text{ (init)}}$ = 25 °C; (2) $T_{j \text{ (init)}}$ = 150 °C; (3) Repetitive Avalanche

Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

9. Thermal characteristics

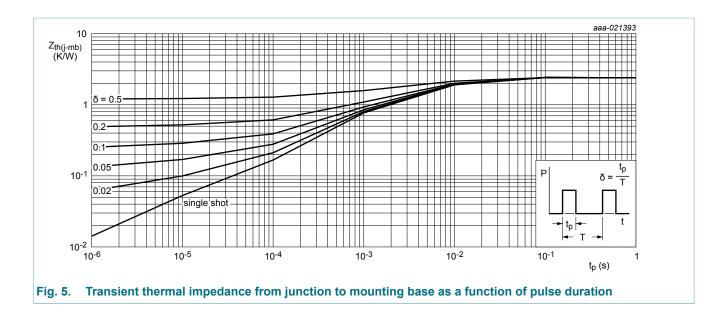
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	2.01	2.43	K/W

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS} drain-source		I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	40	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 ^{\circ}C$	36	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 9; Fig. 10	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	2.45	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10	0.5	-	-	V
I _{DSS} drain	drain leakage current	V _{DS} = 40 V; V _{GS} = 0 V; T _j = 25 °C	-	0.01	1	μΑ
		V _{DS} = 40 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μΑ
I _{GSS}	gate leakage current	V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 5 V; I _D = 15 A; T _j = 25 °C; <u>Fig. 11</u>	-	9.3	11	mΩ
	resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; Fig. 11	-	7.5	9	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 15 \text{ A}; T_j = 175 ^{\circ}\text{C};$ Fig. 12	-	-	22	mΩ
Dynamic ch	naracteristics		ı			
Q _{G(tot)}	total gate charge	I _D = 15 A; V _{DS} = 32 V; V _{GS} = 5 V;	-	13.4	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	3.5	-	nC

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Q_{GD}	gate-drain charge			-	5	-	nC
C _{iss}	input capacitance	V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz;		-	1294	1721	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>		-	175	210	pF
C _{rss}	reverse transfer capacitance			-	91	125	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 2 \Omega; V_{GS} = 5 \text{ V};$ $R_{G(ext)} = 5 \Omega; T_j = 25 \text{ °C}$		-	9.3	-	ns
t _r	rise time			-	15.2	-	ns
t _{d(off)}	turn-off delay time			-	19	-	ns
t _f	fall time	-		-	12.2	-	ns
Source-dra	in diode						
V_{SD}	source-drain voltage	$I_S = 15 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 16$		-	0.85	1.2	V
t _{rr}	reverse recovery time	I_S = 15 A; dI_S/dt = -100 A/ μ s; V_{GS} = 0 V; V_{DS} = 25 V; T_j = 25 °C		-	17.7	-	ns
Q _r	recovered charge			-	9.8	-	nC

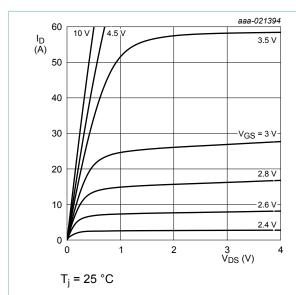


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

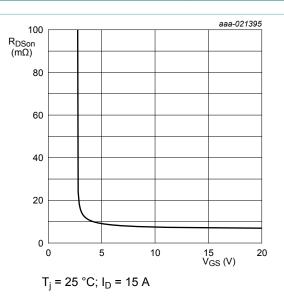


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

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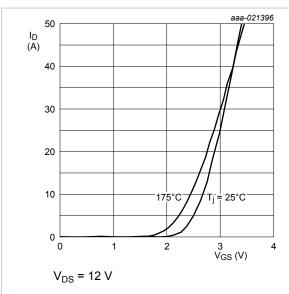


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

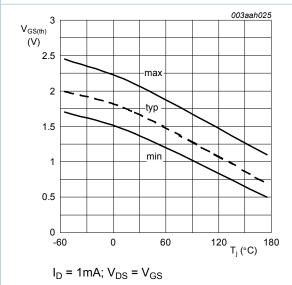


Fig. 10. Gate-source threshold voltage as a function of junction temperature

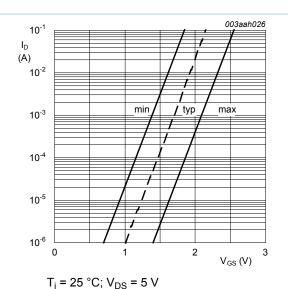


Fig. 9. Sub-threshold drain current as a function of

gate-source voltage

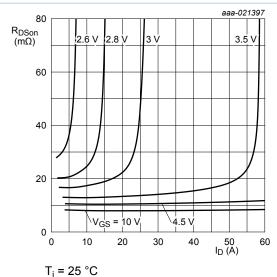


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

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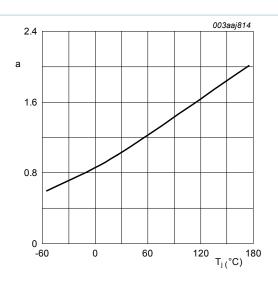


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

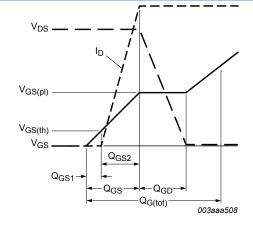
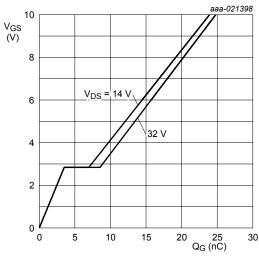
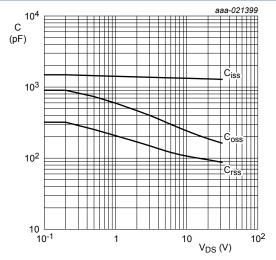


Fig. 14. Gate charge waveform definitions



 $T_i = 25 \,^{\circ}C; I_D = 15 \,^{\circ}A$

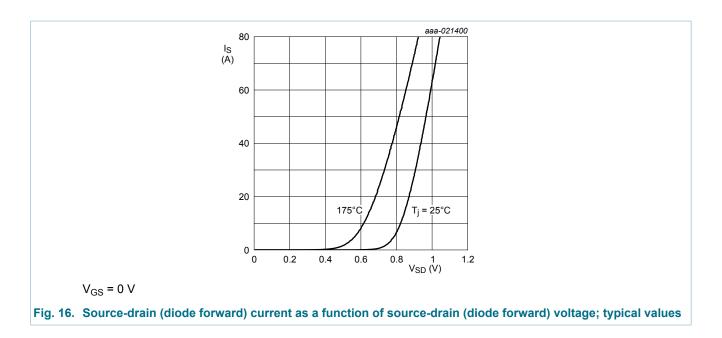
Fig. 13. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0 V$; f = 1 MHz

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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11. Application information

For guidance on how to use and understand this datasheet, please refer to application note AN11158 "Understanding power MOSFET datasheet parameters".

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12. Package outline

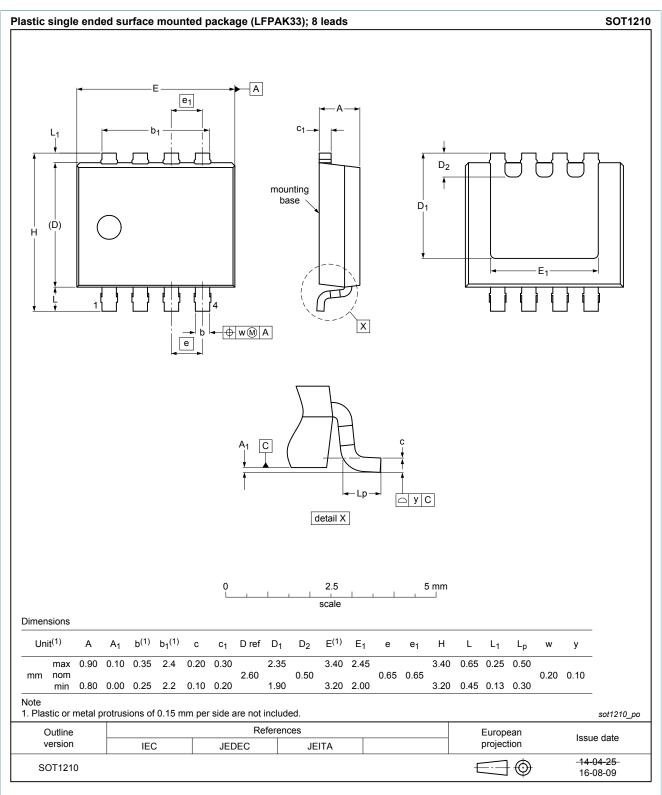


Fig. 17. Package outline LFPAK33 (SOT1210)

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